

Description

The STN8882D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

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TO-252-2L

General Features

 $V_{DS} = 30V I_{D} = 100 A$

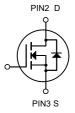
 $R_{DS(ON)} < 5m\Omega$ @ $V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
STN8882D	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings (Tc=25℃ unless otherwise noted)

Symbol	Parameter	Rating	Units	
VDS	Drain- Source Voltage	30	V	
VGS	Gate-Source Voltage	±20	V	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	100	А	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	57	А	
Ідм	Pulsed Drain Current ²	160	Α	
EAS	Single Pulse Avalanche Energy ³	115.2	mJ	
las	Avalanche Current	48	А	
P _D @T _C =25°C	Total Power Dissipation ⁴	53	W	
Тѕтс	Storage Temperature Range	-55 to 175	°C	
TJ	Operating Junction Temperature Range	-55 to 175	°C	
R _θ JA	Thermal Resistance Junction-ambient (Steady State) ¹			
R _θ JA	Thermal Resistance Junction-Ambient ¹ (t ≤10s)		°C/W	
ReJc	Thermal Resistance Junction-Case ¹	2.8	°C/W	



Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVpss	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V
△BVɒss/△Tɹ	BVDSS Temperature Coefficient	•		0.028		V/°C
.Rds(on)		V _{GS} =10V , I _D =30A		3.8	5.5	
.TADS(UN)	Static Drain-Source On- Resistance ²	V _{GS} =4.5V , I _D =15A		7.5	9	mΩ
V _G S(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	1.5	2.5	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient			-6.16		mV/°C
		V _{DS} =24V , V _{GS} =0V ,			1	
IDSS	Drain-Source Leakage Current	T _J =25°C V _{DS} =24V , V _{GS} =0V , T _J =55°C			5	uA
Igss	Gate-Source Leakage Current	V_{GS} = $\pm 20V$, V_{DS} = $0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =30A		22		S
R _g	Gate Resistance	Gate Resistance V _{DS} =0V , V _{GS} =0V , f=1MHz		1.7	3.4	Ω
Qg	Total Gate Charge (4.5V)			20		nC
Q _{gs}	Gate-Source Charge	V _{DS} =15V , V _{GS} =4.5V , I _D =15A		7.6		
Q _{gd}	Gate-Drain Charge			7.2		
T _{d(on)}	Turn-On Delay Time			7.8		ns
Tr	Rise Time	V _{DD} =15V , V _{GS} =10V ,		15		
T _d (off)	Turn-Off Delay Time	-R _G =3.3 -I _D =15A		37.3		
T _f	Fall Time	-1D-13A		10.6		
C _{iss}	Input Capacitance			2295		
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		267		pF
Crss	Reverse Transfer Capacitance	11- 11VII 12		210		
Is	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force			80	Α
Ism	Pulsed Source Current ^{2,5}	Current			160	Α
Vsp	Diode Forward Voltage ²	/oltage ² V _{GS} =0V , I _S =1A , T _J =25°C			1	V
t _{rr}	Reverse Recovery Time	IF=30A , dI/dt=100A/μs ,		14		nS
Qrr	Reverse Recovery Charge	T _J =25°C		5		nC

Note:

^{1.}The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

^{2.}The data tested by pulsed , pulse width .The EAS data shows Max. rating .

^{3.} The test cond $\!\leq$ 300us , duty cycle ition is V_DD=25 $\!\leq$ V,V 2%GS =10V,L=0.1mH,I_AS=53.8A

^{4.}The power dissipation is limited by 175°C junction temperature

^{5.}The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation.



Typical Characteristics

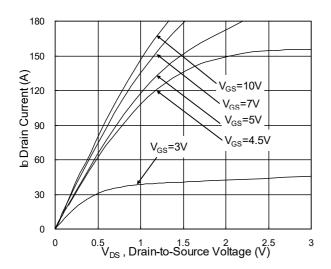


Fig.1 Typical Output Characteristics

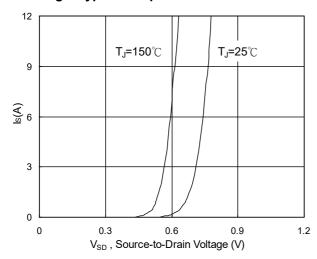


Fig.3 Forward Characteristics of Reverse

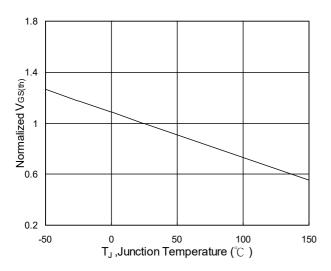


Fig.5 Normalized $V_{\text{GS(th)}}$ vs. T_{J}

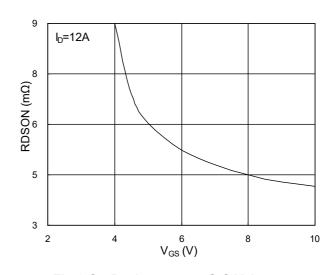


Fig.2 On-Resistance vs. G-S Voltage

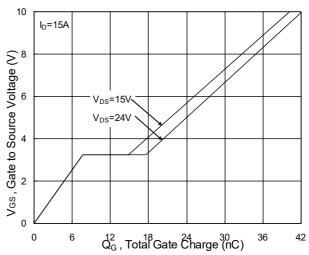


Fig.4 Gate-Charge Characteristics

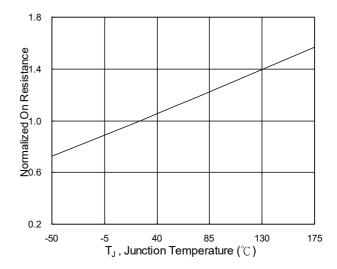
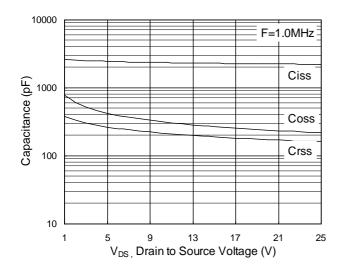


Fig.6 Normalized R_{DSON} vs. T_J



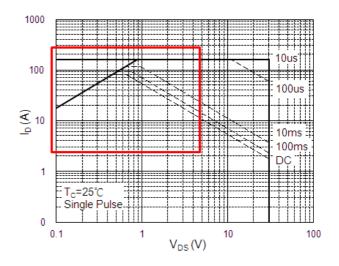


Fig.7 Capacitance

Fig.8 Safe Operating Area

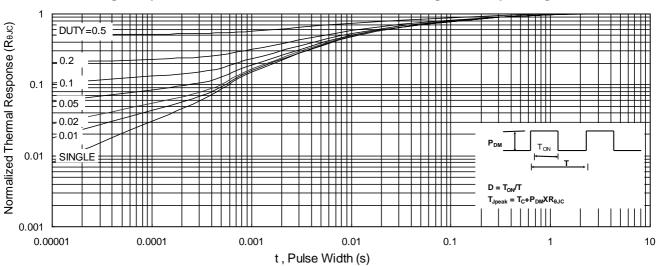
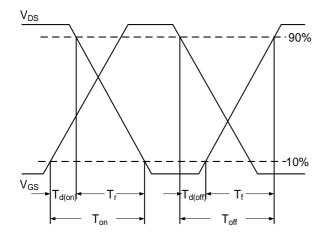


Fig.9 Normalized Maximum Transient Thermal Impedance



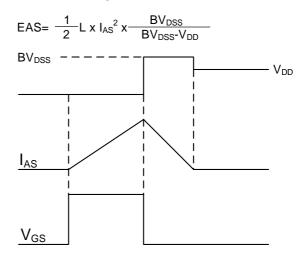
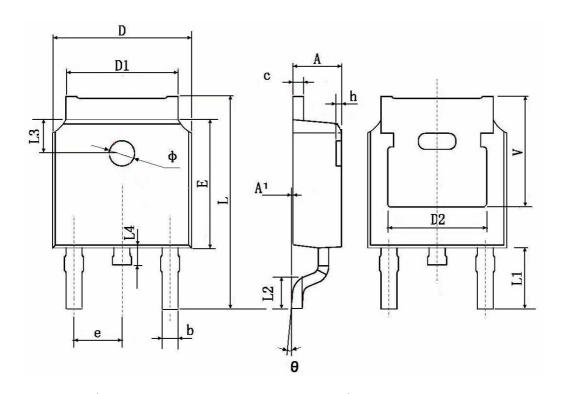


Fig.11 Unclamped Inductive Switching Waveform



TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211 TYP.		



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